









OPA596 JAJSJW5 - JUNE 2024

OPAx596 マルチプレクサ対応入力付き、高電圧 (85V)、低消費電力 (420μA)、 高スルーレート (100V/µs) パワー アンプ

1 特長

- 高いスルーレート: 100V/µs
- 低消費電力:420µA
- 広い電源電圧範囲:
 - ±4V~±42.5V
 - 8V~85V
- MUX 対応入力
- レール ツー レール入出力
- ゲイン帯域幅:3.75MHz
- 低ノイズ:12.8nV/√Hz
- 低い入力バイアス電流:5pA
- 大出力負荷ドライブ: Io ±30mA
- 幅広い温度範囲:-40℃~+125℃
- 業界標準の小型パッケージ:
 - DBV (5ピン SOT-23)
 - DGK (8ピン VSSOP)

2 アプリケーション

- 半導体試験装置
- LCD テスト
- プログラマブル DC 電源
- CT および PET スキャナ
- ソースメジャー ユニット (SMU)
- 光学モジュール
- 実験室およびフィールド用計測機器

3 概要

OPA596 および OPA2596 (OPAx596) は、高電圧 (85V)、高スルーレート (100V/µs)、マイクロパワー (420µA)、ユニティゲイン安定のオペアンプです。

OPAx596 を 使用すると、高ゲイン構成でシステムの出力 電圧を上げることで、半導体試験の出力負荷ドライバやデ ジタル電源などの次世代の高電圧システムを実現できま す。低消費電力と業界標準の小型パッケージにより、サイ ズに制約のある高密度システムで使用でき、システムの熱 管理要件を低減できます。

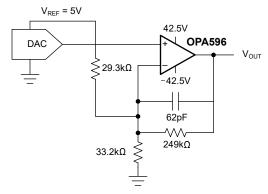
独自の設計手法により、OPAx596 は最小限の消費電力 で非常に高いスルーレートを実現できるため、大信号セト リング タイムが改善され、実効大信号帯域幅が最大化さ れます。また、これらのデバイスはマルチプレクサ対応入 力を備えており、大きな差動電圧 (最大 85V) に対応でき るため、多重化アプリケーションで従来の入力と比較して セトリング動作を向上させるのに役立ちます。

OPAx596 は、業界標準パッケージで供給され、-40°C~ +125℃の温度範囲全体で動作します。

製品情報

部品番号	チャネル	パッケージ ⁽¹⁾
OPA596	シングル	DBV (SOT-23、5)
OPA2596 (2)	デュアル	DGK (VSSOP, 8)

- 詳細については、セクション 10 を参照してください。
- プレビュー情報。



ゲイン付き DAC 出力バッファ



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4 Pin Configuration and Functions

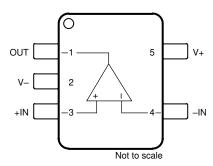


図 4-1. OPA596 DBV Package, 5-Pin SOT-23 (Top View)

表 4-1. Pin Functions: OPA596

PIN		TYPE	DESCRIPTION	
NAME	NO.	IIPE	DESCRIPTION	
+IN	3	Input	Noninverting input	
-IN	4	Input	Inverting input	
OUT	1	Output	Output	
V+	5	Power	Positive (highest) power supply	
V-	2	Power	Negative (lowest) power supply	

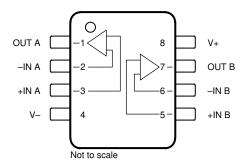


図 4-2. OPA2596 DGK Package, 8-Pin VSSOP (Top View)

表 4-2. Pin Functions: OPA2596

PIN		TYPE	DESCRIPTION	
NAME	NO.	ITPE	DESCRIPTION	
+IN A	3	Input	Noninverting input, channel A	
+IN B	5	Input	Noninverting input, channel B	
–IN A	2	Input	Inverting input, channel A	
–IN B	6	Input	Inverting input, channel B	
OUT A	1	Output	Output, channel A	
OUT B	7	Output	Output, channel B	
V+	8	Power	Positive (highest) power supply	
V-	4	Power	Negative (lowest) power supply	



5 Specifications

5.1 Absolute Maximum Ratings

Over operating free-air temperature range (unless otherwise noted)(1)

			MIN MA	X UNIT
V	Supply voltage	Dual supply	±46	.5 V
V _S	Supply voltage	Single supply, $V_S = (V+) - (V-)$		V 93
	Signal input pin voltage ⁽²⁾	Common-mode	(V-) - 0.3 (V+) + 0	.3 V
	Signal input pin voltage(=)	Differential	(V+) – (V	
	Input current, all pins ⁽²⁾		±	0 mA
I _{SC}	Output short circuit ⁽³⁾	Output short circuit ⁽³⁾		ıs
TJ	Junction temperature		1:	o °C
T _{STG}	Storage temperature		-65 1:	°C

- 1) Operation outside the Absolute Maximum Ratings may cause permanent device damage. Absolute Maximum Ratings do not imply functional operation of the device at these or any other conditions beyond those listed under Recommended Operating Conditions. If used outside the Recommended Operating Conditions but within the Absolute Maximum Ratings, the device may not be fully functional, and this may affect device reliability, functionality, performance, and shorten the device lifetime.
- (2) Input terminals are diode-clamped to the power-supply rails. Input signals that can swing more than 0.3V beyond the supply rails must be current-limited to 10mA or less.
- (3) Short-circuit to ground.

5.2 ESD Ratings

				VALUE	UNIT
V		Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±1500	V
\ \(\(\)	ESD)		Charged-device model (CDM), per ANSI/ESDA/JEDEC JS-002 ⁽²⁾	±500	\ \ \

- (1) JEDEC document JEP155 states that 500V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250V CDM allows safe manufacturing with a standard ESD control process.

5.3 Recommended Operating Conditions

Over operating free-air temperature range (unless otherwise noted)

			MIN	NOM MAX	UNIT
V Supply voltage		Dual supply	±4	±42.5	V
V _S Supply voltage	Supply voltage	Single supply	8	85	V
T _A	T _A Ambient temperature		-40	125	°C

5.4 Thermal Information

		OPA596	OPA2596	
	THERMAL METRIC ⁽¹⁾	DBV (SOT-23)	DGK (VSSOP)	UNIT
		5 PINS	8 PINS	
R _{0JA}	Junction-to-ambient thermal resistance	165.4	143.6	°C/W
R ₀ JC(top)	Junction-to-case (top) thermal resistance	99.1	50.4	°C/W
R _{θJB}	Junction-to-board thermal resistance	64.5	78.7	°C/W
ΨЈТ	Junction-to-top characterization parameter	42.6	3.0	°C/W
ΨЈВ	Junction-to-board characterization parameter	64.2	77.5	°C/W
R _{0JC(bot)}	Junction-to-case (bottom) thermal resistance	N/A	N/A	°C/W

 For more information about traditional and new thermal metrics, see the <u>Semiconductor and IC Package Thermal Metrics</u> application report.

資料に関するフィードバック(ご意見やお問い合わせ)を送信

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5.5 Electrical Characteristics

at V_S = 85V (±42.5V), T_A = 25°C, R_L = 10k Ω to mid-supply, and V_{CM} = V_{OUT} = mid-supply (unless otherwise noted)

		PARAMETER	TEST CONDITIONS		MIN	TYP	MAX	UNIT	
	OFFSET	VOLTAGE							
	Vos	Input offset voltage				±0.2	±1	mV	
Part Part	dV _{OS} /dT	Input offset voltage drift	T _A = -40°C to +125°C			±1	±6	μV/°C	
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	PSRR		8V ≤ V _S ≤ 85V			±1	±5	μV/V	
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	INPUT BI	AS CURRENT		,			 		
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$						±5	±10	nΛ	
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	I_B	Input bias current	T _A = -40°C to +85°C				±50	þΑ	
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$			T _A = -40°C to +125°C				±1	nA	
Input offset current T _A = -40°C to +85°C ±50 T _A = -40°C to +125°C ±1 nA						±5	±10	nΛ	
Input voltage noise F = 0.1Hz to 10Hz 1.4 μV _{PP}	Ios	Input offset current	T _A = -40°C to +85°C				±50	þΑ	
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$			T _A = -40°C to +125°C				±1	nA	
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	NOISE								
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$		Input voltage noise	f = 0.1Hz to 10Hz			1.4		μV _{PP}	
$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$			f = 100Hz			17.8			
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	e _n	Input voltage noise density	f = 1kHz			12.9		nV/\sqrt{Hz}	
NPUT VOLTAGE NPUT VOLTAGE Common-mode voltage Linear operation $(V-) - 0.1$ $(V+) - 3.5$ V CMRR Common-mode rejection $(V-) \le V_{CM} \le (V+) - 3.5V$ 126 140 140 dB NPUT IMPEDANCE Differential 100 2.5 MMQ pF Common-mode 100 5.5 GQ pF OPEN-LOOP GAIN V 134 140			f = 10kHz			12.8			
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	i _n	Current noise density	f = 1kHz			10		fA/√Hz	
$ \begin{array}{ c c c c c c c } \hline & & & & & & & & & & & & & & & & & & $	INPUT VO	DLTAGE		,			<u>'</u>		
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	V _{CM}	Common-mode voltage	Linear operation		(V-) - 0.1		(V+) - 3.5	V	
	CMDD	Common made rejection	0/)<)/ < 0/) 25/		126	140		٩D	
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	CIVIRR	Common-mode rejection	$(V-) \le V_{CM} \le (V+) - 3.5V$	T _A = -40°C to +125°C	124	140		uБ	
Common-mode 10 5.5 GΩ pF OPEN-LOOP GAIN A _{OL} Open-loop voltage gain (V-) + 1V < V _O < (V+) - 1.5V, R _L = 10kΩ to mid-supply 134 140 140 V-) + 3V < V _O < (V+) - 3.5V, R _L = 2kΩ to mid-supply 126 126 126 FREQUENCY RESPONSE 6 = 1 2.25 126 GBW Gain-bandwidth product G = 10 3 MHz GR Slew rate G = ±1, V _O = 70V step 100 V/μs SS Settling time To ±0.01%, G = -1, V _O = 10V step, C _L = 100pF 2 μs THD+N Total harmonic distortion + G = ±1 V _O = 70V step = 1kHz R _L = 10kΩ -102 dB	INPUT IM	PEDANCE					<u>'</u>		
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$		Differential				100 2.5		MΩ pF	
$A_{OL} = \begin{array}{ c c c c c c }\hline & & & & & & & & & & & & & & & & & & &$		Common-mode				10 5.5		GΩ pF	
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	OPEN-LC	OOP GAIN							
$ \begin{array}{c} A_{OL} \\ A_{OL} \\ \\ A_{OL} \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\$			$(V-) + 1V < V_O < (V+) - 1.5V,$		134	140			
	۸	Open leen veltage gein	$R_L = 10k\Omega$ to mid-supply	$T_A = -40^{\circ}\text{C to } +125^{\circ}\text{C}$	120	140		٩D	
$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$	AOL	Open-loop voltage gain	$(V-) + 3V < V_O < (V+) - 3.5V,$			126		uБ	
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$			$R_L = 2k\Omega$ to mid-supply	$T_A = -40^{\circ}\text{C to } +125^{\circ}\text{C}$		126			
GBW Gain-bandwidth product $G = 10$ 3 MHz GBW G = 100 3.75 3.75 SR Slew rate $G = \pm 1$, $V_0 = 70V$ step 100 V/μ s Se Settling time $To \pm 0.01\%$, $G = -1$, $V_0 = 10V$ step, $C_L = 100pF$ 2 μ s Overload recovery $G = -1$ 115 ns TOtal harmonic distortion + $G = \pm 1$, $V_0 = 70V_{CR}$, $f = 1kHz$ $R_L = 10k\Omega$ -102	FREQUE	NCY RESPONSE							
$G = 100$ 3.75 SR Slew rate $G = \pm 1$, $V_O = 70V$ step 100 V/μs SS Settling time $T_O \pm 0.01\%$, $G = -1$, $V_O = 10V$ step, $C_L = 100$ pF 2 μs Overload recovery $G = -1$ 115 ns Total harmonic distortion + $G = \pm 1$, $V_O = 70V_{CD}$, $f = 1$ kHz $R_L = 10$ kΩ -102			G = 1			2.25			
SR Slew rate $G = \pm 1$, $V_O = 70V$ step 100 V/ μ s S Settling time $T_O \pm 0.01\%$, $G = -1$, $V_O = 10V$ step, $C_L = 100pF$ 2 μ s Overload recovery $G = -1$ 115 ns	GBW	Gain-bandwidth product G = 10				3		MHz	
Settling time To $\pm 0.01\%$, G = -1 , V _O = $10V$ step, C _L = 100 pF 2 μ s Overload recovery G = -1 115 n s Total harmonic distortion + $G = \pm 1$ V _O = $70V_{CR}$, $f = 1kHz$ $R_L = 10k\Omega$ -102			G = 100			3.75			
Overload recovery $G = -1$ 115 ns Total harmonic distortion + $G = +1$ $V_0 = 70$ V_{CD} $f = 1$ kHz $R_L = 10$ k Ω -102	SR	Slew rate	G = ±1, V _O = 70V step			100		V/µs	
Total harmonic distortion + $G = +1$ $V_0 = 70$ V_{CD} $f = 1$ kHz $R_L = 10$ k Ω -102	t _S	Settling time	To ±0.01%, G = -1, V _O = 10V	step, C _L = 100pF		2		μs	
$G = +1$ $V_0 = 70$ V_{00} $t = 1$ kHz		Overload recovery	G = -1			115		ns	
noise $R_L = 2k\Omega$ -95	THD±N	Total harmonic distortion +	G = +1 \/_ = 70\/_ f = 1\/_	$R_L = 10k\Omega$		-102		dB	
	אידטווו	noise	0 - +1, v ₀ - 10v _{pp} , 1 - 1KHZ	$R_L = 2k\Omega$		-95		aB	



5.5 Electrical Characteristics (続き)

at V_S = 85V (±42.5V), T_A = 25°C, R_L = 10k Ω to mid-supply, and V_{CM} = V_{OUT} = mid-supply (unless otherwise noted)

PARAMETER	TEST CONDITIONS		MIN	TYP	MAX	UNIT
					•	
	No load			12	50	mV
, ,	R_L = 10kΩ to mid-supply			100	435	IIIV
	$R_L = 2k\Omega$ to mid-supply			500	2.05	V
Output current				±30		mA
Capacitive load drive				1		nF
Open-loop output impedance				550		Ω
IT LIMIT					1	
SUPPLY						
0	L - 0A			420	490	
Quiescent current	IO = UIIIA	T _A = -40°C to +125°C			500	μA
ATURE	1				1	
Overtemperature	Shutdown temperature			185		°C
shutdown				20		C
	Voltage output swing from rail Output current Capacitive load drive Open-loop output impedance T LIMIT SUPPLY Quiescent current ATURE Overtemperature	$\begin{tabular}{lll} Voltage output swing from rail & No load \\ $R_L = 10k\Omega$ to mid-supply \\ $R_L = 2k\Omega$ to mid-supply \\ \hline $Output$ current & $Capacitive$ load drive \\ \hline $Open-loop$ output impedance & T LIMIT \\ $SUPPLY$ & $Quiescent$ current & $I_O = 0mA$ \\ \hline $ATURE$ & $Overtemperature & $Shutdown$ temperature \\ \hline \end{tabular}$	$\begin{tabular}{lll} Voltage output swing from rail & No load & $R_L = 10k\Omega \ to mid-supply & $R_L = 2k\Omega \ to mid-supply & $R_L = $	$\begin{tabular}{lll} Voltage output swing from rail & No load \\ R_L = 10k\Omega \ to \ mid-supply \\ R_L = 2k\Omega \ to \ mid-supply \\ \hline Output \ current & \\ Capacitive load drive & \\ \hline Open-loop output impedance & \\ \hline T \ LIMIT & \\ \hline SUPPLY & \\ \hline Quiescent \ current & I_O = 0 mA & \\ \hline T_A = -40 \ C \ to +125 \ C & \\ \hline ATURE & \\ \hline Overtemperature & Shutdown \ temperature & \\ \hline \end{tabular}$	$\begin{tabular}{ l l l l l l l l l l l l l l l l l l l$	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$



6 Detailed Description

6.1 Overview

The OPAx596 are low power ($420\mu A$), high-slew rate ($100V/\mu s$), 85V operational amplifiers (op amps). These op amps uses a proprietary design technique to achieve a very high slew capability with minimal power consumption. The OPAx596 is capable of driving $\pm 30mA$ of output current and can swing to within 100mV of either power supply rail.

The amplifiers feature state-of-the-art CMOS technology and advanced design features that help achieve outstanding ac performance and enable small package options. The OPAx596 strengths also include 3.75MHz bandwidth, 12.8nV/√Hz noise spectral density, and low input bias current. These features make the OPAx596 an exceptional choice to gain or buffer the output of a digital-to-analog converter (DAC) in digitally programmable power supplies.

6.2 Functional Block Diagram

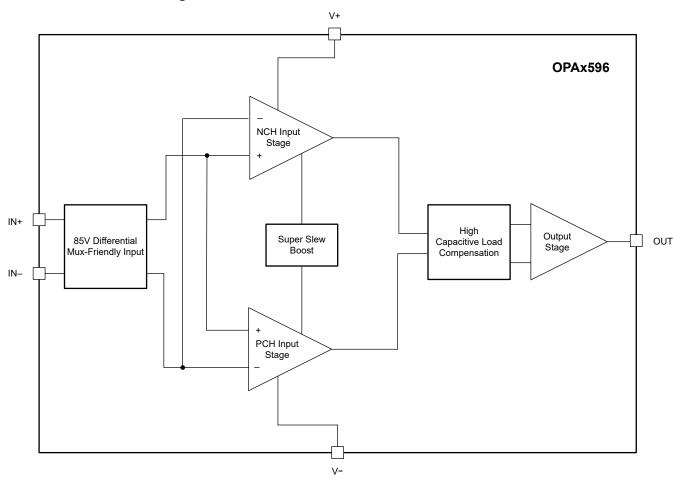


図 6-1. Functional Block Diagram

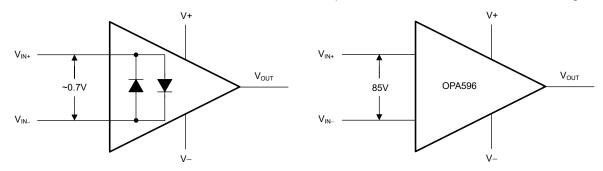
English Data Sheet: SBOSA42



6.3 Feature Description

6.3.1 Mux-Friendly Inputs

The OPAx596 use a unique input architecture to eliminate the need for input protection diodes but still provide robust input protection under transient conditions. Conventional input diode protection schemes shown in \boxtimes 6-2 can be activated by fast transient step responses and can introduce signal distortion and settling time delays because of alternate current paths, as shown in \boxtimes 6-3. For low-gain circuits, these fast-ramping input signals forward-bias back-to-back diodes that cause an increase in input current and result in extended settling time.



Conventional Input Protection Limits Differential Input Range

OPA596 Provides Full 85V Differential Input Range

図 6-2. OPA596 Input Protection Does Not Limit Differential Input Capability

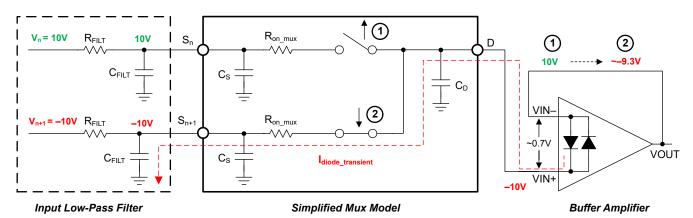


図 6-3. Back-to-Back Diodes Create Settling Issues

The OPAx596 feature a true high-impedance differential input capability for high-voltage applications. This patented input protection architecture does not introduce additional signal distortion or delayed settling time, making these devices an excellent choice for multichannel, high-switched, input applications. The OPAx596 tolerate a maximum differential swing (voltage between inverting and noninverting pins of the op amp) of up to 85V, making these devices a great choice for use as a comparator or in applications with fast-ramping or switched input signals.



6.3.2 Thermal Protection

The OPAx596 has a thermal protection feature that prevents damage from self heating. When the junction temperature (T_J) reaches approximately 180°C, the op amp output stage disables. This thermal protection works by monitoring the temperature of the output stage and turning off the op amp output drive. Thermal protection forces the output to a high-impedance state. The OPAx596 is designed with approximately 30°C of thermal hysteresis and returns to normal operation when the output stage temperature becomes less than approximately 150°C.

This thermal protection is not designed to prevent this device from exceeding absolute maximum ratings, but rather from excessive thermal overload.

6.3.3 Slew Boost

Slew rate is the maximum rate of change of output voltage change with respect to time and is typically specified in units of volts per microsecond, V/µs. The OPAx596 can enter a slew condition when a large, rapid moving signal is applied at the input. While slewing, the op amp enters an open loop condition and significant slew induced distortion can be seen on the output signal.

 \pm 1 shows that the slew rate of an op amp is typically determined by the saturation current of the input stage, I_{SAT} , and the compensation capacitor, C_C .

$$SR = \frac{I_{SAT}}{C_C} \tag{1}$$

The slew rate scales with the quiescent current, I_Q , of the op amp. There are several ways that designers have overcome slew rate limitation. For example, decompensation improves slew rate at the expense of stability by lowering C_C . More commonly, modern op amps are equipped with slew boost technology that increases I_{SAT} to overcome the inherent slew rate limitations. Slew boost circuits can vary in implementation, but designers can typically expect about a 4 × improvement over comparable unboosted op amps.

The OPAx596 uses a proprietary design to achieve an unprecedented slew rate to I_Q ratio. The novel slew boost technology in OPAx596 provides a nearly 100 × slew rate improvement over comparable unboosted op amps.

6.3.4 Overload Recovery

Overload recovery is defined as the time required for the op amp output to recover from a saturated state to a linear state. The output devices of the op amp enter a saturation region when the output voltage exceeds the rated operating voltage, either due to the high input voltage or the high gain. After the device enters the saturation region, the charge carriers in the output devices require time to return back to the linear state. After the charge carriers return back to the linear state, the device begins to slew at the specified slew rate. Thus, the propagation delay in case of an overload condition is the sum of the overload recovery time and the slew time.

6.4 Device Functional Modes

The OPAx596 has a single functional mode and is operational when the power-supply voltage is between 8V (±4V) and 85V (±42.5V).

English Data Sheet: SBOSA42



7 Application and Implementation

注

以下のアプリケーション情報は、TIの製品仕様に含まれるものではなく、TIではその正確性または完全性を保証いたしません。個々の目的に対する製品の適合性については、お客様の責任で判断していただくことになります。お客様は自身の設計実装を検証しテストすることで、システムの機能を確認する必要があります。

7.1 Application Information

The OPAx596 are low power $(420\mu A)$, high-slew rate $(100V/\mu s)$, 85V power operational amplifiers (op amps). These op amps use a proprietary design technique to achieve a very high slewing capability while consuming minimal power. The low power consumption helps reduce heat generation on the board while the output swings near the supply rail. The high slew reduces slew related distortion at the output when dealing with large peak, high frequency signals.

7.2 Typical Applications

7.2.1 Bridge-Connected Piezoelectric Driver

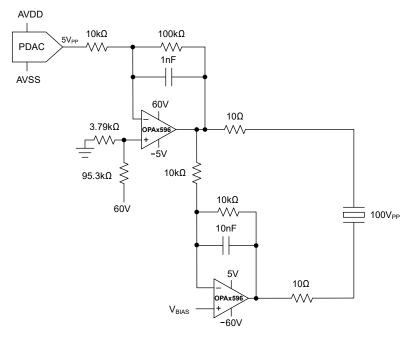


図 7-1. 100V_{PP} Piezoelectric Driver With Bridge Connected Load

資料に関するフィードバック(ご意見やお問い合わせ) を送信

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7.2.1.1 Design Requirements

The OPAx596 is used to drive a piezoelectric actuator with a 100V operating range at a frequency of 100Hz. The large capacitance inherent to the piezoelectric actuator can cause undesired ringing of the driver amplifier. An inaccurate response of the actuator is possible due in part to amplifier instability. Adequate phase margin for a 500nF equivalent load is necessary for a robust driver circuit for the piezoelectric actuator presented here.

表 7-1. Design Parameters

PARAMETER	VALUE
Positive supply voltage	60V
Negative supply voltage	-5V
Piezoelectric actuator capacitance (1kHz)	500nF
Piezoelectric operating voltage range	0V to 100V
Operating frequency	100Hz
DAC output voltage	5V _{PP}

7.2.1.2 Detailed Design Procedure

Piezoelectric actuators offer many benefits over traditional solenoid counterparts. Piezoelectric actuators are more precise, power efficient, and smaller in general when compared to solenoid actuators. One challenge with piezoelectric actuators is that the piezoelectric actuators operate over a very wide voltage range. Driving voltages of more than 60V are not uncommon, and can easily reach hundreds of volts. The OPAx596 operate with a supply voltage of up to 85V.

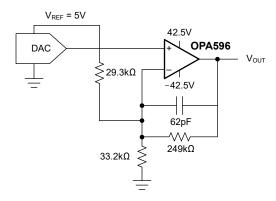
In this design example, the OPAx596 are used to provide a 100V_{PP} signal to control a high-voltage piezoelectric actuator (see also 🗵 7-1). The piezoelectric actuator can be modeled as a large capacitor when operated at less than the resonant frequency. The piezoelectric actuator is treated as a floating load driven by two op amps of the OPAx596. The outputs of the op amps are set to be 180° out-of-phase to essentially double the voltage seen by the actuator load.

The signal voltage of the digital-to-analog converter is applied a 10V/V gain by the OPAx596. A simple voltage divider provides a 2.5V reference to level shift the output to create a unipolar driving voltage. An isolation resistor improves phase margin and stability. Add a small 10Ω R_{ISO} at the output of the OPAx596.

English Data Sheet: SBOSA42



7.2.2 DAC Output Gain and Buffer



7.2.2.1 Design Requirements

The OPAx596 is designed for use as an output driver stage with gain and provides a wide, bipolar supply voltage. Combined with the small size of the SOT23-5 package and the low power consumption, these features make this device a great choice for high-channel density systems, such as semiconductor test and manufacturing platforms where many channels are present. In this design example, the OPAx596 is configured for a gain of approximately 17V/V.

表 7-2. Design Parameters

PARAMETER	VALUE
Supply voltage	-42.5V to +42.5V
Input voltage	0V to 5V
Output voltage	-42.5V to +42.5V
Gain	17V/V

7.2.2.2 Detailed Design Procedure

In this design example, the OPAx596 is configured as both a gain stage and output driver. The input signal to the amplifier is 0V to 5V, and the device is configured with a noninverting gain of 17V/V. The DAC reference voltage of 5V is used as a reference to enable a bipolar output swing. This configuration results in an output voltage of -42.5V to +42.5V. This design example is common in many systems that use a DAC to provide the input signal and require a wide output signal with low output current requirements. The OPAx596 can swing to either rail while remaining within the thermally specified limits. Such systems include test and measurement platforms and power supplies.

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7.2.3 Single-Supply Piezoelectric Driver

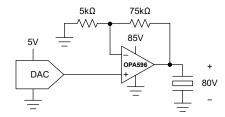


図 7-2. 80V Single-Supply Piezoelectric Driver

7.2.4 High-Side Current Sense

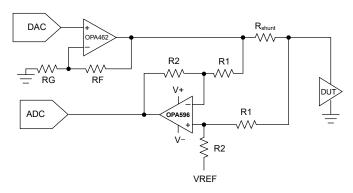


図 7-3. 100V High-Side Current Sense

7.2.5 High-Voltage Instrumentation Amplifier

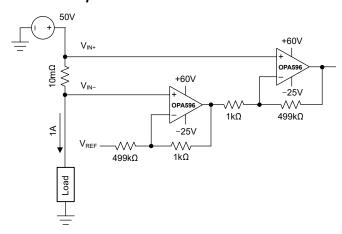


図 7-4. High-Voltage Instrumentation Amplifier

English Data Sheet: SBOSA42



7.2.6 Composite Amplifier

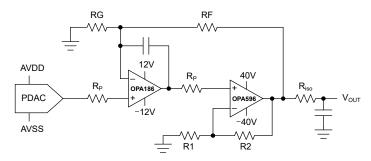


図 7-5. High-Precision, High-Voltage Output Composite Amplifier

7.3 Power Supply Recommendations

The OPAx596 operates from power supplies up to ±42.5V (85V), and as little as ±4V (8V) with excellent performance. Most behavior remains unchanged throughout the full operating voltage range. A power-supply bypass capacitor of at least 0.1µF is required for proper operation. Ensure that the capacitor voltage is rated for high voltage across the full operating temperature range. Some applications do not require an equal positive and negative output voltage swing. The OPAx596 can be powered with asymmetrical supplies.

7.4 Layout

7.4.1 Layout Guidelines

For best operational performance of the device, use good PCB layout practices, including the following quidelines:

- Noise can propagate into analog circuitry through the power pins of the op amp and the circuit as a whole.
 Connect low-ESR, 0.1µF ceramic bypass capacitors between each supply pin and ground. Place the capacitors as close to the device as possible. A single bypass capacitor from V+ to ground is sufficient for single supply applications.
- Separate grounding for analog and digital portions of circuitry is one of the simplest and most effective
 methods of noise suppression. One or more layers on multilayer PCBs are usually devoted to ground planes.
 A ground plane helps distribute heat and reduces EMI noise pickup. Make sure to physically separate digital
 and analog grounds paying attention to the flow of the ground current.
- To reduce parasitic coupling, run the input traces as far away from the supply or output traces as possible. If these traces cannot be kept separate, crossing the sensitive trace perpendicular is much better as opposed to in parallel with the noisy trace.
- Place the external components as close to the device as possible.
- Keep the length of input traces as short as possible. Always remember that the input traces are the most sensitive part of the circuit.
- Consider a driven, low-impedance guard ring around the critical traces. A guard ring can significantly reduce leakage currents from nearby traces that are at different potentials.
- Clean the PCB following board assembly for best performance.
- Any precision integrated circuit can experience performance shifts due to moisture ingress into the plastic
 package. Following any aqueous PCB cleaning process, baking the PCB assembly is recommended to
 remove moisture introduced into the device packaging during the cleaning process. A low temperature, post
 cleaning bake at 85°C for 30 minutes is sufficient for most circumstances.

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7.4.1.1 Thermal Considerations

Through normal operation, the op amps can self-heat. Self-heating is a natural increase in the die junction temperature that occurs in every amplifier. This self-heating is a result of several factors, including quiescent power consumption, package thermal resistance, PCB layout, and device operating conditions.

Operate the OPAx596 within the rated junction temperature, T_J , range to avoid thermal shutdown. Use the $\gtrsim 2$ to determine the estimated T_J

$$T_I = P_D \times \theta J_A + T_A \tag{2}$$

In a quiescent state, P_D is given by the product of the power supply and the quiescent current of the op amp. $\stackrel{\Rightarrow}{\Rightarrow}$ 3 shows the calculation of T_J for the OPAx596 assuming an 85V power supply is used and an operating temperature of 25°C.

$$T_I = (85V \times 490\mu A) \times 165.4^{\circ} \frac{C}{W} + 25^{\circ} C \tag{3}$$

$$T_I = 31.89^{\circ}C \tag{4}$$

The low power consumption of the OPAx596 causes minimal self-heating even in a small SOT23-5 package as given by $\stackrel{>}{\pi}$ 4. In a loaded condition, P_D is equal to addition of the quiescent power, P_{DQ} and the power dissipated by the output stage, P_{DL} . The worst-case condition is given when the output voltage is equal to $\frac{1}{2}$ of either supply rail (assuming symmetrical supplies, V+ and V-). In a worst-case condition, P_{DL} is given by $\stackrel{>}{\pi}$ 5.

$$P_{DL} = \frac{\left(V + \right)^2}{4 \times R_I} \tag{5}$$

For example, assume the OPAx596 is powered with bipolar ± 42.5 V power supplies and drives a 5kΩ load, R_L, to ground. The maximum increase in T_J is expected to be about 22°C as given by \pm 6. In this example, to keep the op amp within the *Absolute Maximum Ratings*, operate in T_A well under 128°C to account for different factors.

$$\Delta T_I = (41.7mW + 90.3mW) \times 165.4 \frac{^{\circ}C}{W}$$
 (6)



7.4.2 Layout Example

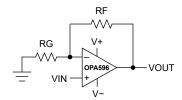


図 7-6. Schematic Representation of Noninverting Configuration

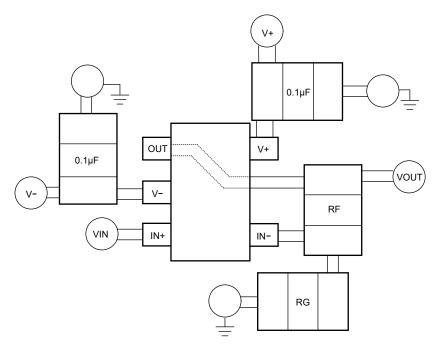


図 7-7. Board Layout for Noninverting Configuration of the SOT23-5 Package



8 Device and Documentation Support

TI offers an extensive line of development tools. Tools and software to evaluate the performance of the device, generate code, and develop solutions are listed below.

8.1 ドキュメントの更新通知を受け取る方法

ドキュメントの更新についての通知を受け取るには、www.tij.co.jp のデバイス製品フォルダを開いてください。[通知] をクリックして登録すると、変更されたすべての製品情報に関するダイジェストを毎週受け取ることができます。 変更の詳細については、改訂されたドキュメントに含まれている改訂履歴をご覧ください。

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8.5 用語集

テキサス・インスツルメンツ用語集 この用語集には、用語や略語の一覧および定義が記載されています。

9 Revision History

資料番号末尾の英字は改訂を表しています。その改訂履歴は英語版に準じています。

DATE	REVISION	NOTES
June 2024	*	Initial Release

10 Mechanical, Packaging, and Orderable Information

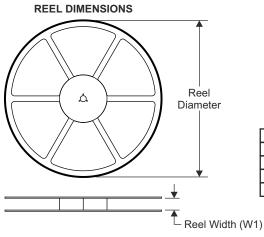
The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

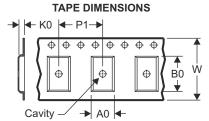
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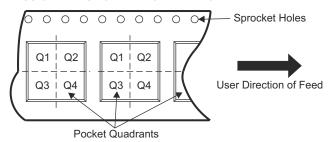
10.1 Tape and Reel Information





Α0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

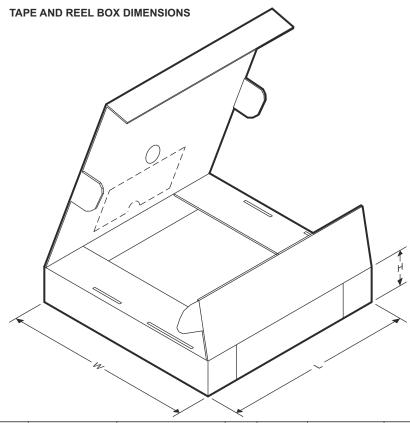
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
OPA596DBVR	SOT-23	DBV	5	3000	180.0	8.4	3.23	3.17	1.37	4.0	8.0	Q3
OPA596DBVT	SOT-23	DBV	5	250	180.0	8.4	3.23	3.17	1.37	4.0	8.0	Q3

English Data Sheet: SBOSA42





Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
OPA596DBVR	SOT-23	DBV	5	3000	213.0	191.0	35.0
OPA596DBVT	SOT-23	DBV	5	250	223.0	270.0	35.0

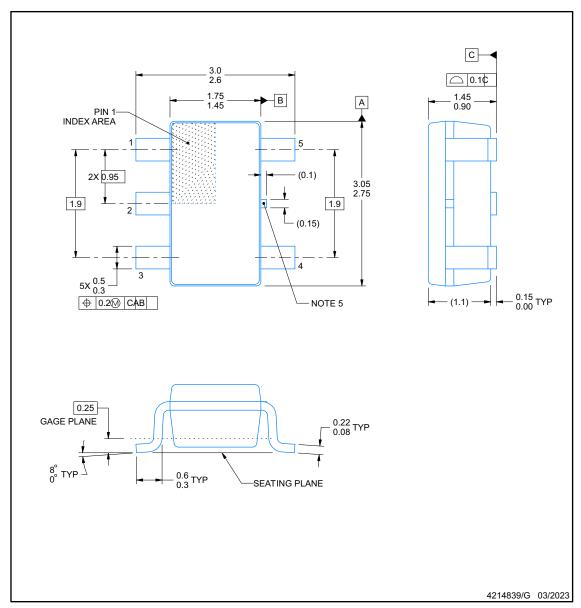


DBV0005A

PACKAGE OUTLINE

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

- Reference JEDEC MO-178.
 Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.25 mm per side.
 Support pin may differ or may not be present.



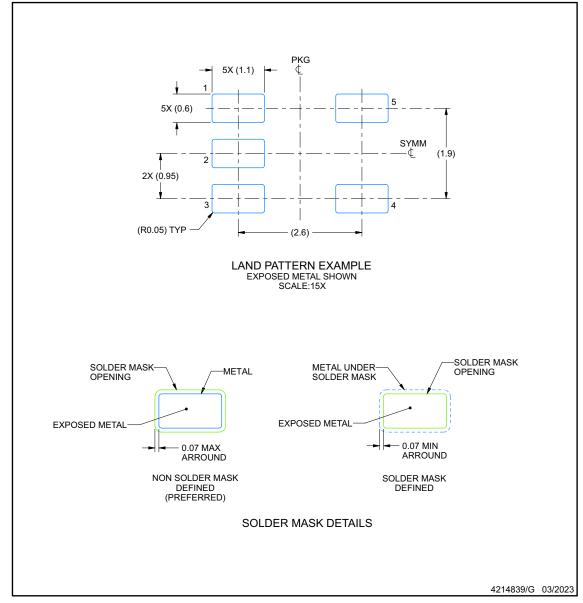


EXAMPLE BOARD LAYOUT

DBV0005A

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



NOTES: (continued)

- 6. Publication IPC-7351 may have alternate designs.
- 7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



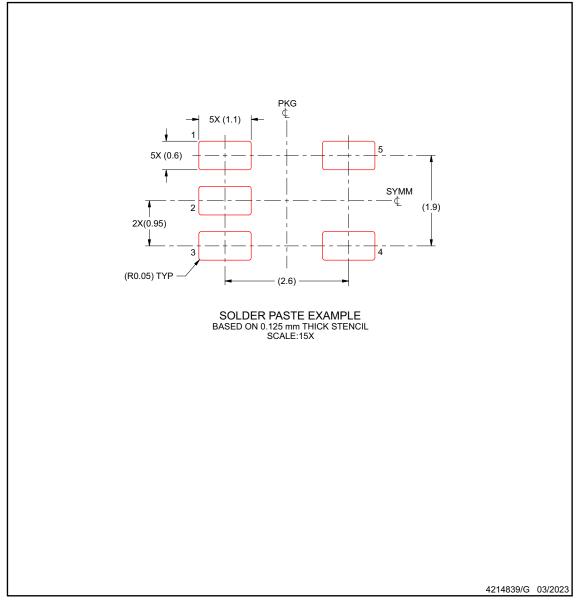


EXAMPLE STENCIL DESIGN

DBV0005A

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.9. Board assembly site may have different recommendations for stencil design.



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PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
POPA596DBVR	ACTIVE	SOT-23	DBV	5	3000	TBD	Call TI	Call TI	-40 to 125		Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

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- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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SMALL OUTLINE TRANSISTOR



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
 2. This drawing is subject to change without notice.
 3. Reference JEDEC MO-178.

- 4. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.25 mm per side.
- 5. Support pin may differ or may not be present.



SMALL OUTLINE TRANSISTOR



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE TRANSISTOR



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



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